PROTON

JSC “Proton”

MOSFET chip Maxima-46S

Description

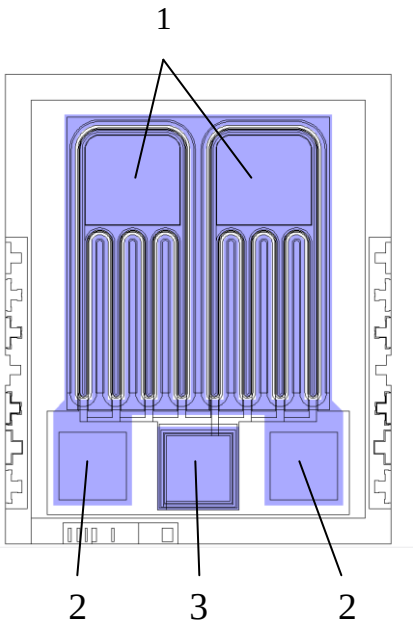
MOSFET chip with induced channel (normally-off, double drain) Maxima-46S is designed to be used in hybrid microchips and packaged field-effect transistors.

Feature

- Chip size – 0.74 x0.9 mm
- Chip thickness – 0.36±0.02 mm
- Contact pads size:
  Drain – 0.182 mm x 0.171 mm
  Gate – 0.13 x0.133 mm
  Source – 0.13 x 0.13 mm
- Metallization: top – AlSi,
  bottom – Si

Absolute Maximum Ratings

Maximum Temperature	
Storage Temperature	-55°C to150°C
Operating Junction Temperature	-40°C to100°C
Maximum Voltages	
Drain-Source Voltage	±90V
Gate-Source Voltage	±20V



1 - Drain
2 - Source
3 - Gate

Electrical characteristics (T_A = 25°C)

Parameter	Symbol	Unit	Min.	Typ.	Max.	Conditions
Drain-Source Breakdown Voltage	BV_{DS}	V	±90	±100		V_{GS} = 0 V, I_{D} = 100 μA
Gate-Source Leakage Current	I_{GSS}	nA			100	V_{GS} = 20 V, V_{DS} = 0 V
ON-State Drain Current	$I_{D\ (ON)}$	mA	100	150		V_{GS}= 6 V, V_{DS}=25 V
Drain-Drain Leakage Current	$I_{D\ Leak}$	nA		0.9	3.0	V_{GS} = 0 V, V_{DS} =±90 V
Drain-to-Drain ON-State Resistance	$R_{DD\ (ON)}$	Ohm		45	60	V_{GS} = 6 V, I_{D}=±20 mA
Output Drain-Drain Capacitance	$C_{OSS(OFF)}$	pF		6.0		V_{DS} = 0 V, V_{GS}= 0 V *

* Measured in the packaged device.